

FMBSA06

NPN General Purpose Amplifier

- This device is designed for general purpose amplifier applications at WWW.DZSG.GON collector currents to 300 mA.
- Sourced from Process 12.



Absolute Maximum Ratings* T_a=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	80	V	
V _{CBO}	Collector-Base Voltage	80	V	
V_{EBO}	Emitter-Base Voltage	4.0	V	
I _C	Collector Current - Continuous	500	mA	
T _J , T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C	

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Characte	eristics	AND STELLES			
V _{(BR)CEO}	Collector-Emitter Sustaining Voltage *	$I_C = 1.0 \text{mA}, I_B = 0$	80		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	4.0		V
I _{CEO}	Collector Cut-off Current	$V_{CE} = 60V, I_{B} = 0$		0.1	μΑ
I _{CBO}	Collector Cut-off Current	$V_{CB} = 80V, I_{E} = 0$		0.1	μΑ
On Characte	eristics				
h _{FE}	DC Current Gain	I _C = 10mA, V _{CE} = 1.0V	100		
		$I_C = 100 \text{mA}, V_{CE} = 1.0 \text{V}$	100		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 100 \text{mA}, I_B = 10 \text{mA}$		0.25	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 10mA, V _{CE} = 1.0V		1.2	V
Small Signa	I Characteristics			- nZ	, U - "
f _T	Current Gain Bandwidth Product	$I_C = 10 \text{mA}, V_{CE} = 2.0 \text{V}, f = 100 \text{MHz}$	100		MHz
Pulse Test: Pulse	e Width ≤ 300μs, Duty Cycle ≤ 2.0%				

Thermal Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
P _D	Total Device Dissipation *	700	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, total	180	°C/W

^{*} Device mounted on a 1 in 2 pad of 2 oz copper.

These ratings are based on a maximum junction temperature of 150 degrees C.
These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Typical Characteristics

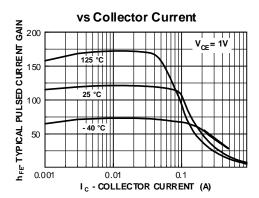


Figure 1. Typical Pulsed Current Gain vs Collector Current

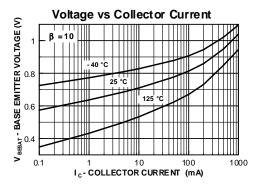


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

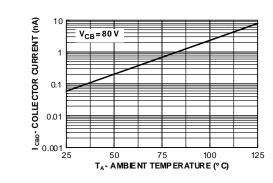


Figure 5. Collector Cutoff Current vs Ambient Temperature

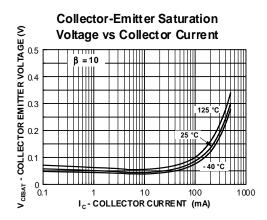


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

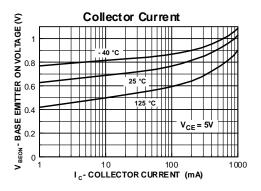


Figure 4. Base-Emitter On Voltage vs Collector Current

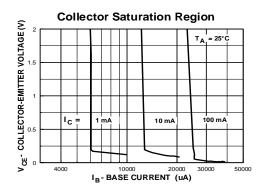


Figure 6. Collector Saturation Region

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Typical Characteristics (Continued)

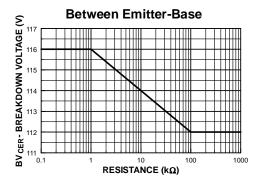


Figure 7. Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base

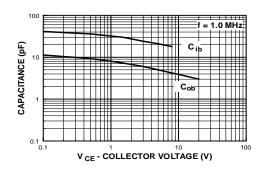


Figure 8. Input and Output Capacitance vs Reverse Voltage

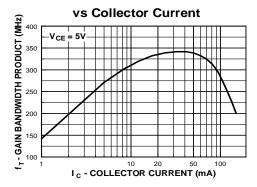


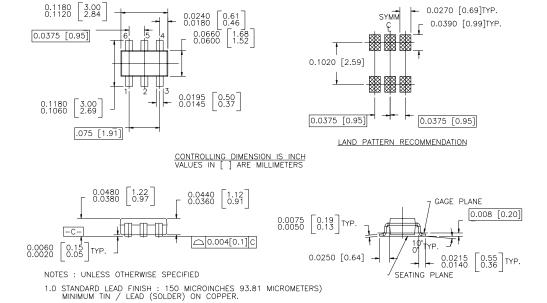
Figure 9. Gain Bandwidth Product vs Collector Current

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Package Dimensions

2.0 NO JEDEC REGISTRATION AS OF JULY 1996

SuperSOT™-6



SUPER SOT 6 LEADS

Dimensions in Millimeters

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